

OM SENI

ESD9X3.3ST5G Series, Transient Voltage Suppressors

Micro-Packaged Diodes for ESD Protection

The ESD9X Series is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

Specification Features:

- Low Clamping Voltage
- Small Body Outline Dimensions:
0.039" x 0.024" (1.0 mm x 0.60 mm)
- Low Body Height: 0.017" (0.43 mm) Max
- Stand-off Voltage: 3.3 V – 12 V
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- These are Pb-Free Devices

Mechanical Characteristics:

LEAD FINISH: 100% Matte Sn (Tin)

MOUNTING POSITION: Any

QUALIFIED MAX REFLOW TEMPERATURE: 260°C

Device Meets MSL 1 Requirements

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD)	Contact Air	± 30 ± 30	kV
ESD Voltage	Per Human Body Model Per Machine Model	16 400	kV V
Total Power Dissipation on FR-5 Board (Note 1) @ $T_A = 25^\circ\text{C}$	P_D	150	mW
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
Lead Solder Temperature – Maximum (10 Second Duration)	T_L	260	$^\circ\text{C}$



PIN 1. CATHODE
2. ANODE



SOD-923
CASE 514AA

MARKING DIAGRAM



X = Specific Device Code
M = Date Code

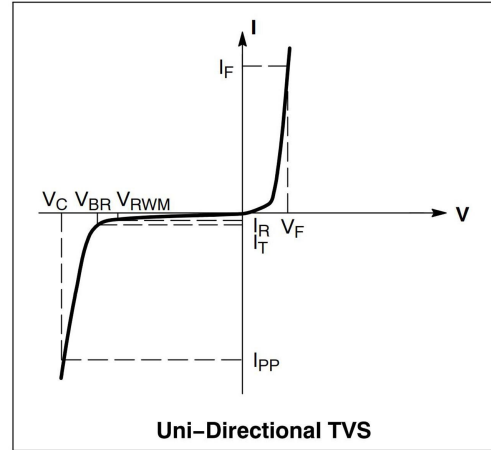
OM SENI

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current
I _F	Forward Current
V _F	Forward Voltage @ I _F
P _{pk}	Peak Power Dissipation
C	Max. Capacitance @ V _R = 0 and f = 1 MHz

*See Application Note AND8308/D for detailed explanations of datasheet parameters.



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted, V_F = 1.1 V Max. @ I_F = 10 mA for all types)

Device*	Device Marking	V _{RWM} (V)	I _R (μA) @ V _{RWM}	V _{BR} (V) @ I _T (Note 2)	I _T	Max I _{PP} (A) (Note 3)	V _C (V) @ Max I _{PP} (Note 3)	P _{pk} (W) (8 x 20 μs)	C (pF)	V _C
		Max	Max	Min	mA		Max	Typ	Typ	Per IEC61000-4-2 (Note 4)
ESD9X3.3ST5G	A	3.3	2.5	5.0	1.0	9.8	10.4	102	80	Figures 1 and 2 (Note 5)
ESD9X5.0ST5G	B	5.0	1.0	6.2	1.0	8.7	12.3	107	65	
ESD9X7.0ST5G	5**	7.0	0.1	7.5	1.0	4.0	25	100	65	
ESD9X12ST5G	C	12	1.0	13.5	1.0	5.9	23.7	140	30	

* Include SZ-prefix devices where applicable.

**Rotated 270 degrees.

2. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.

3. Surge current waveform per Figure 5.

4. For test procedure see Figures 3 and 4 and Application Note AND8307/D.

5. ESD9X5.0ST5G shown below. Other voltages available upon request.

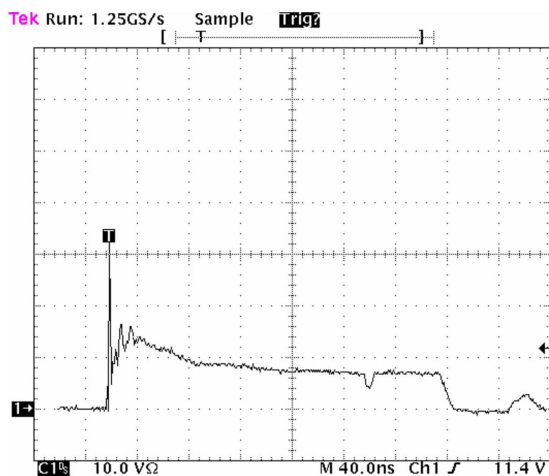


Figure 1. ESD Clamping Voltage Screenshot
Positive 8 kV contact per IEC 61000-4-2

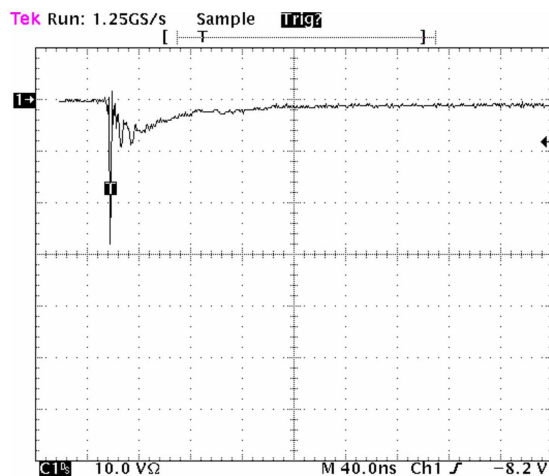


Figure 2. ESD Clamping Voltage Screenshot
Negative 8 kV contact per IEC 61000-4-2

OM SENI

IEC 61000-4-2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

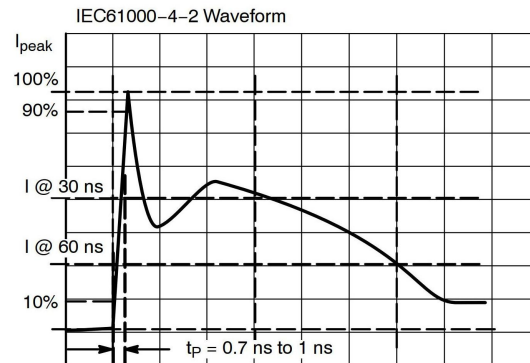


Figure 3. IEC61000-4-2 Spec

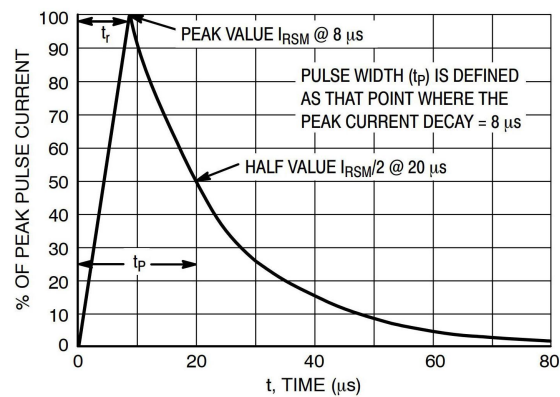


Figure 5. 8 X 20 μ s Pulse Waveform

TYPICAL CHARACTERISTICS

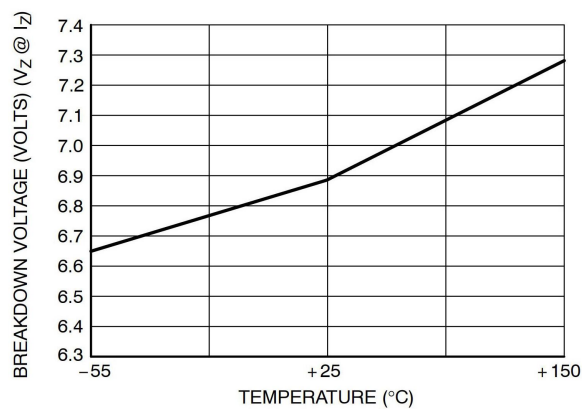


Figure 6. Typical Breakdown Voltage versus Temperature

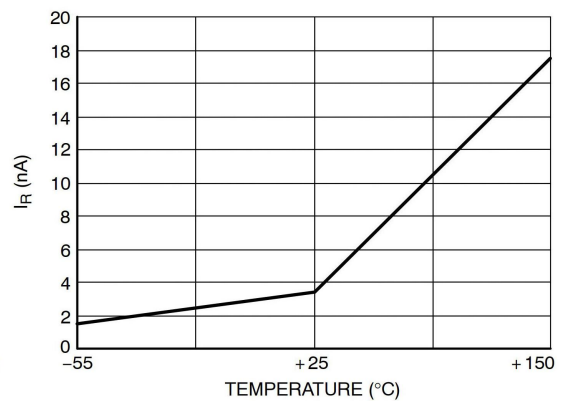


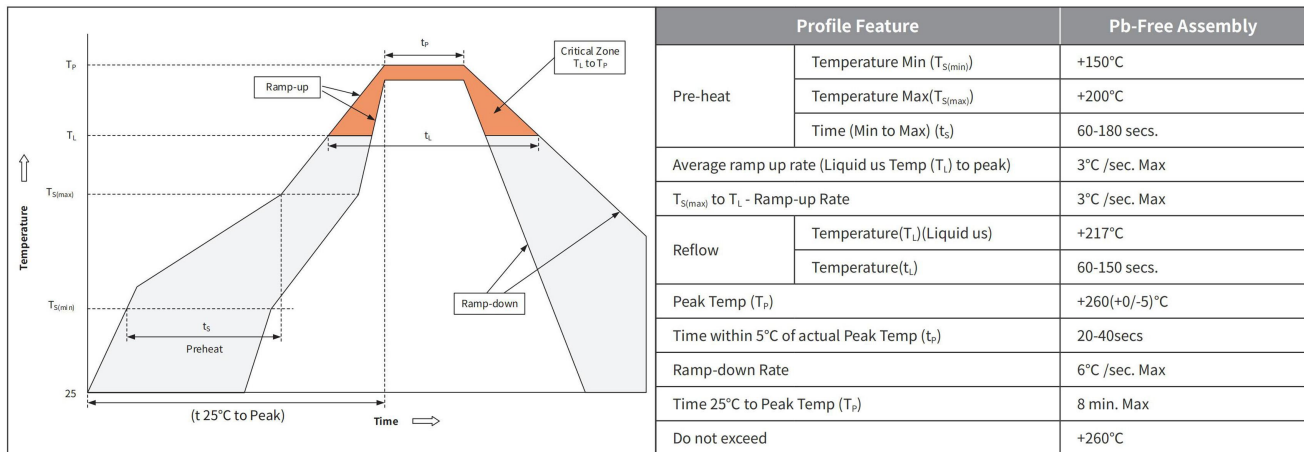
Figure 7. Typical Leakage Current versus Temperature

OM SENI

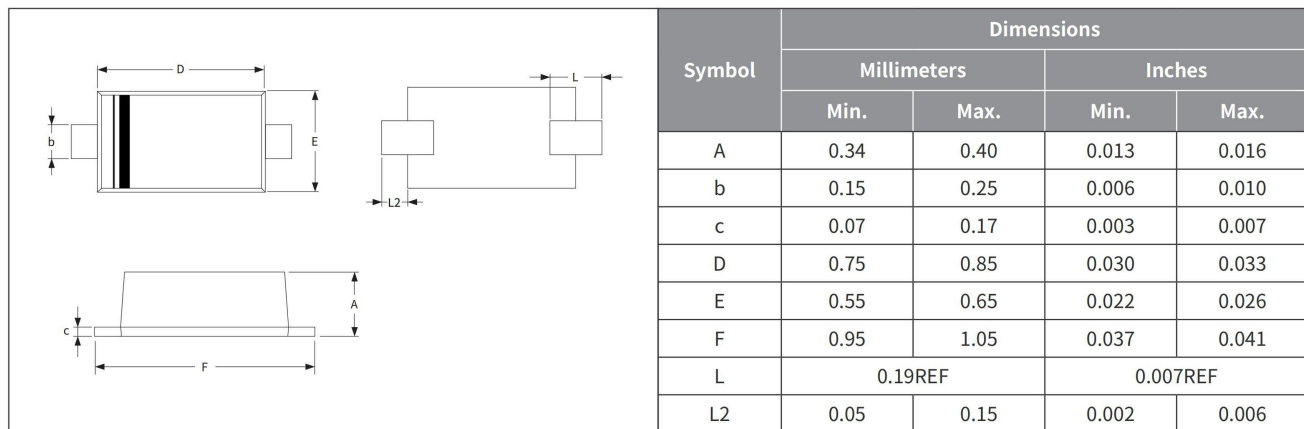
Ordering Information

PREFERRED P/N	PACKAGE	SIZE(mm)	DELIVERY MODE	MPQ(PCS)
	SOD-923	1.00×0.60×0.37	7"	8000

Recommended Soldering Conditions



Package Outline Dimensions (SOD-923)



Suggested Pad Layout

